

PATENT  
81784.0182  
DRAFT AMENDMENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

YONEDA et al.

Serial No: 09/148,606

Filed: September 4, 1998

For: Semiconductor Device Having Laser  
Annealed Semiconductor Device, Display  
Device and Liquid Crystal Display Device

Art Unit: 2674

Examiner: A. Zamani

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DRAFT AMENDMENT UNDER 37 C.F.R.  
§ 1.116

Box AF  
Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Final Office Action dated August 13, 2001, time for response to which has been extended three months by the enclosed Petition from November 13, 2001 to February 13, 2002, please amend the above-referenced application as follows:

IN THE CLAIMS:

Please replace the text of claims 1, 3, 5, 9-10, 14, 17-18, and 20-22 with the following text:

1. (Amended) A semiconductor device in which a plurality of semiconductor elements are formed on a substrate, wherein

in some or all of said semiconductor elements, a channel width of a channel region formed in a semiconductor layer to which laser annealing is applied is larger than a channel length thereof, and a channel width direction is neither vertical to nor parallel with regard to a side direction of said substrate.